

third insulating film defined in Claim 5 to form an opening so that said cap conductive film is exposed;

burying a conductive material in said opening to form a plug; and

forming an upper wiring, which extends on said plug, on said second insulating film defined in Claim 1, said third insulating film defined in Claim 4 or said third insulating film defined in Claim 5.

7. (Amended) A method for manufacturing a semiconductor integrated circuit device according to Claim 1, 2, 3, 4 or 5 wherein said wiring defined in Claim 1 or said second wiring defined in any one of Claims 2 to 5 is made of copper, silver, aluminum or an alloy containing these metals as a main component.

In the Specification:

Please replace the original specification with the attached Substitute Specification.

REMARKS

This amendment is in response to the Office Action dated October 26, 2001.

By the present amendment, claims 6 and 7 have been converted into multiple dependent format claims in light of limitations in the claims referring to more than one preceding